TOSHIBA FAST RECOVERY DIODE SILICON DIFFUSED TYPE

100FXG13, 100FXH13

HIGH SPEED RECTIFIER APPLICATIONS

Unit in mm

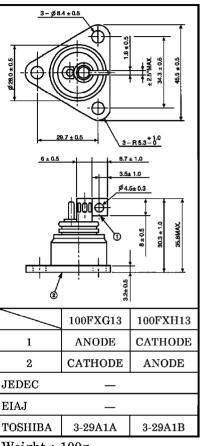
Repetitive Peak Reverse Voltage : VRRM=3000V

Average Forward Current $: I_{F(AV)} = 100A$

Reverse Recovery Time ($T_i = 25$ °C) : $t_{rr} = 2.5 \mu s$

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Repetitive Peak Reverse Voltage	v_{RRM}	3000	V	
Non-Repetitive Peak Reverse Voltage (Non-Repetitive ≤ 5 ms, $T_j = 0 \sim 125$ °C)	$v_{ m RSM}$	3000	V	
Average Forward Current	I _{F (AV)}	100	A	
Peak One Cycle Surge Forward Current (Non-Repetitive) IFSM		2000 (50Hz)	A	
		2200 (60Hz)		
Junction Temperature Range	T_{j}	-40~125	$^{\circ}\mathrm{C}$	
Storage Temperature Range	$T_{ m stg}$	-40~125	$^{\circ}\mathrm{C}$	
Screw Torque	_	1.6	N∙m	



Weight: 100g

ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITION		MIN.	MAX.	UNIT		
Repetitive Peak Reverse Current	I_{RRM}	$V_{RRM} = 3000V, T_j = 125^{\circ}C$		_	30	mA		
Peak Forward Voltage	$v_{ extbf{FM}}$	$I_{FM} = 320A \ (T_j = 25^{\circ}C)$		_	1.8	V		
Reverse Recovery Time		$I_{ m F} = 100 A$	$T_j = 25^{\circ}C$	_	2.5			
		$di_F/dt = 100A/\mu s$	$T_j = 125$ °C	_	3.0	μ s		
Thermal Resistance	$ m R_{th~(j-c)}$	Junction to Case		_	0.2	°C/W		

Note : Contact thermal resistance $R_{th (c-f)} = 0.07^{\circ}C/W$ (Applied silicone grease)

[■] TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.

The information contained herein is subject to change without notice.

